

Title (en)  
DRILLING BIT

Publication  
**EP 0096591 A3 19840711 (EN)**

Application  
**EP 83303312 A 19830608**

Priority  
ZA 824008 A 19820608

Abstract (en)  
[origin: EP0096591A2] In a diamond impregnated bit scourer particles in the form of silicon carbide are added to the matrix. The mesh size of the silicon carbide is less than that of diamond and the concentration preferably about 40, if the diamond concentration is 40.

IPC 1-7  
**E21B 10/46**; B24D 3/00; B24D 3/34

IPC 8 full level  
**B24D 3/06** (2006.01); **B24D 3/34** (2006.01); **E21B 10/46** (2006.01)

CPC (source: EP)  
**B24D 3/06** (2013.01); **B24D 3/342** (2013.01); **E21B 10/46** (2013.01)

Citation (search report)

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